

1 TO-92 1. Emitter 2. Base 3. Collector

NPN Epitaxial Silicon Transistor

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	35	V
/ _{CEO}	Collector-Emitter Voltage	30	V
V _{EBO}	Emitter-Base Voltage	4	V
с	Collector Current	30	mA
Pc	Collector Power Dissipation	250	mW
Г _Ј	Junction Temperature	150	°C
T _{STG}	Storage Temperature	-55 ~ 150	°C

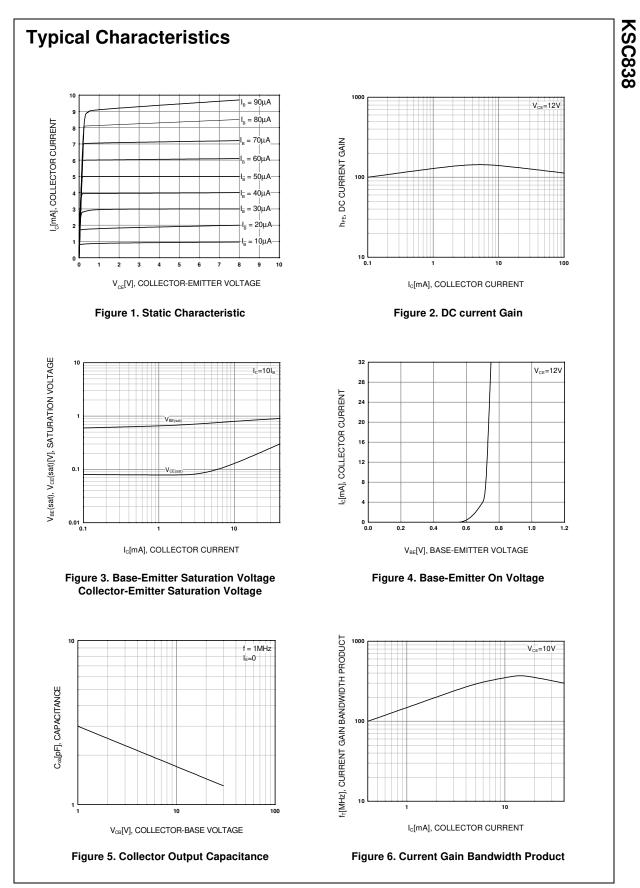
Absolute Maximum Ratings $T_a=25^{\circ}C$ unless otherwise noted

Electrical Characteristics T_a=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV _{CBO}	Collector-Base Breakdown Voltage	I _C =100μA, I _E =0	35			V
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C =5mA, I _B =0	30			V
BV _{EBO}	Emitter-Base Breakdown Voltage	I _E =10μA, I _C =0	4			V
I _{CBO}	Collector Cut-off Current	V _{CB} =30V, I _E =0			0.1	μA
I _{EBO}	Emitter Cut-off Current	V _{EB} =4V, I _C =0			0.1	μA
h _{FE}	DC Current Gain	V _{CE} =12V, I _C =2mA	40		240	
V _{BE} (on)	Base-Emitter On Voltage	V _{CE} =6V, I _C =1mA	0.65	0.70	0.75	V
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I _C =10mA, I _B =1mA		0.1	0.4	V
f _T	Current Gain Bandwidth Product	V _{CE} =10V, I _C =1mA	100	250		MHz
C _{ob}	Output Capacitance	V _{CB} =10V, I _E =0, f=1MHz		2.0	3.2	pF

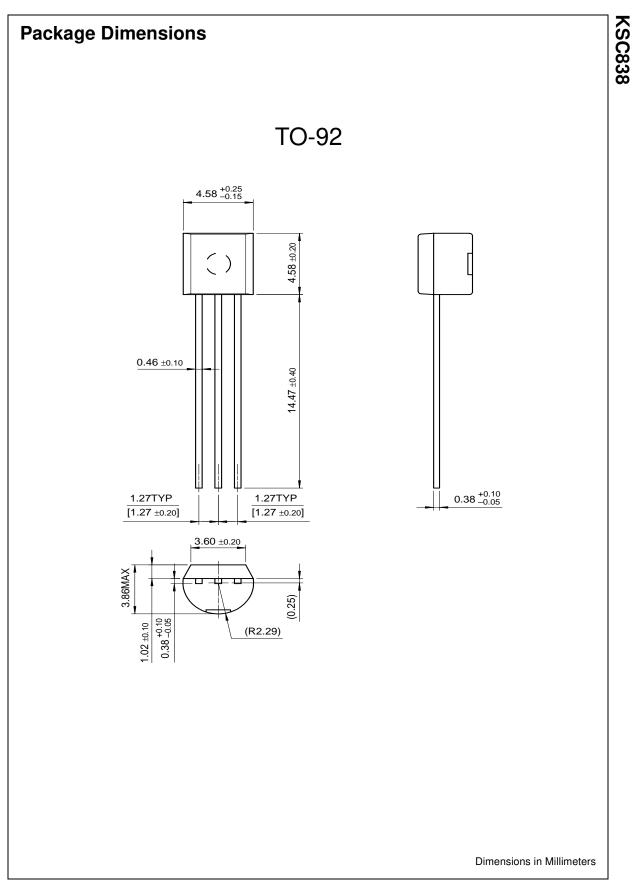
h_{FE} Classification

Classification	R	0	Y
h _{FE}	40 ~ 80	70 ~ 140	120 ~ 240



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